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Product Specification

1003.360901

Part Number	Customer				
Category OverallWafer	Parameter		Specification	Measurement Method	
	1.0	Diameter	100.00 +/- 0.50 mm		
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Wafer Vendor	
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor	
	4.0	Secondary Flat Orientation	none/semi std		
	5.0	Overall Thickness	300.00 +/- 5.00 μm	ADE, 100%	
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process	
	7.0	Bow	<60.00µm	ADE to ASTM F534, 20%	
	8.0	Warp	<60.00µm	ADE to ASTM F657, 20%	
	9.0	Edge Chips	0	Bright Light, 100% (note 2)	
	10.0	Edge Exclusion	5mm		
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor	
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor	
	13.0	Handle Thickness	300.00 +/- 5.00 μm	ADE, 100%	
	14.0	Handle Doping Type	Any	Wafer Vendor	
	15.0	Handle Dopant	Any	Wafer Vendor	
	16.0	Handle Resistivity	0.01 - 50 Ohmcm	Wafer Vendor	
	17.0	Backside Finish	Polished with lasermark.	Guaranteed by process	
	18.0	Total scratch length	None	Bright Light, 100% (note 2)	
	19.0	Surface Haze	none	Bright Light, 100% (note 2)	

Icemos Technology Ltd

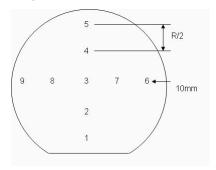
Product Specification

1003.360901

Part Number		Customer		
Category	Parameter	Specification	Measurement Method	
Shipping Details	Wafer per box :	Max 25		
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging		
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspect	tion performed using microscope scan as below. 5x objective.		

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information